Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Extended temperature range T_i = 175 °C
- · Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	100	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	1.2	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 1.2 A; T_j = 25 °C		-	285	385	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D
2	D	drain		
3	G	gate	0 -1 -1 -2 -3	G ← F ★ \
4	S	source	SC-74; TSOP6 (SOT457)	\ \\ \pi \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\
5	D	drain	, , , , , , , , , , , , , , , , , , , ,	
6	D	drain		s
				017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package	^P ackage						
	Name	Description	Version					
PMN280ENEA	SC-74; TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457					

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN280ENEA	3P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	100	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	1.2	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	0.9	Α
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	667	mW
			[1]	-	1.7	W
		T _{sp} = 25 °C		-	7.5	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drai	n diode			l .		
Is	source current	T _{amb} = 25 °C	[1]	-	1.2	Α
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V
Avalanche r	ruggedness			1		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	T _{j(init)} = 25 °C; I _D = 0.16 A; DUT in valanche (unclamped)		-	8.4	mJ

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm 2 .
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.

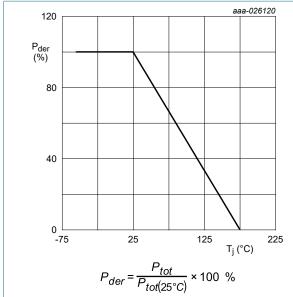


Fig. 1. Normalized total power dissipation as a function of junction temperature

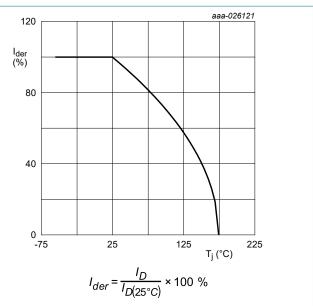


Fig. 2. Normalized continuous drain current as a function of junction temperature

100 V, N-channel Trench MOSFET

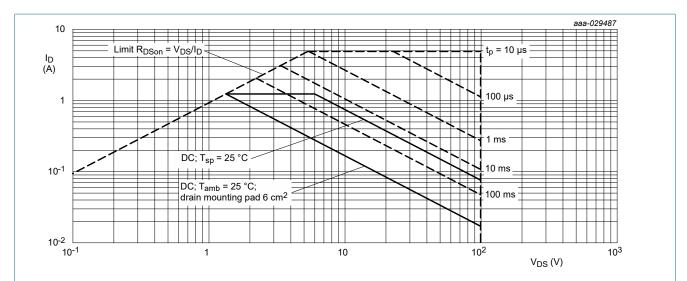


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	195	225	K/W
junctio	junction to ambient	nction to ambient	[2]	-	78	90	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

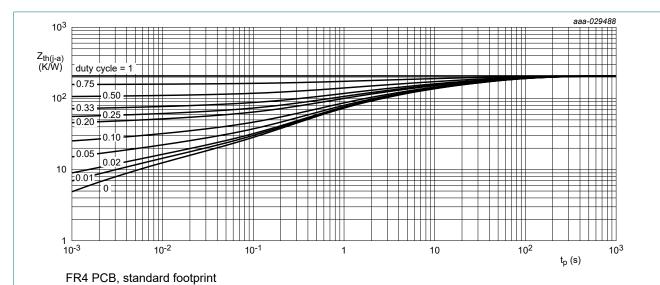


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

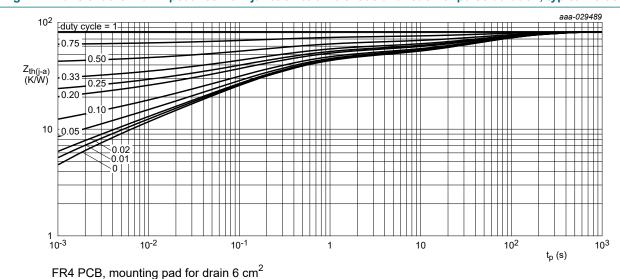


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

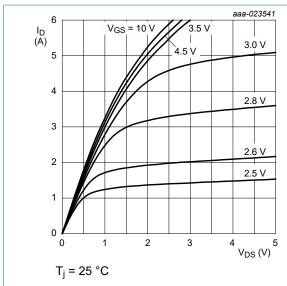
10. Characteristics

Table 7. Characteristics

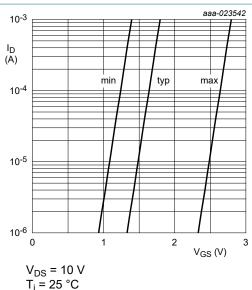
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	15	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-15	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 1.2 A; T _j = 25 °C	-	285	385	mΩ
	resistance	V _{GS} = 10 V; I _D = 1.2 A; T _j = 175 °C	-	798	1078	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 1.2 \text{ A}; T_j = 25 \text{ °C}$	-	301	432	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 1.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	5.2	-	S
R_{G}	gate resistance	f = 1 MHz	-	1.8	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 50 V; I _D = 1.2 A; V _{GS} = 10 V;	-	4.5	6.8	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.5	-	nC
Q_{GD}	gate-drain charge		-	1.1	-	nC
C _{iss}	input capacitance	V _{DS} = 50 V; f = 1 MHz; V _{GS} = 0 V;	-	190	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	13	-	pF
C _{rss}	reverse transfer capacitance		-	9	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; I _D = 1.2 A; V _{GS} = 10 V;	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
t _{d(off)}	turn-off delay time	- 	-	10	-	ns
t _f	fall time		-	3	-	ns
Source-dra	in diode		'	,		,
V _{SD}	source-drain voltage	I _S = 1.2 A; V _{GS} = 0 V; T _j = 25 °C	-	8.0	1.2	V
t _{rr}	reverse recovery time	I _S = 1.1 A; dI _S /dt = -100 A/µs;	-	20	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}; T_j = 25 \text{ °C}$	-	11	-	nC

Product data sheet

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Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}\text{C}$

Subthreshold drain current as a function of Fig. 7. gate-source voltage

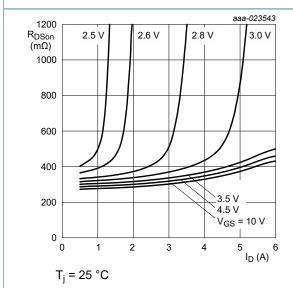


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

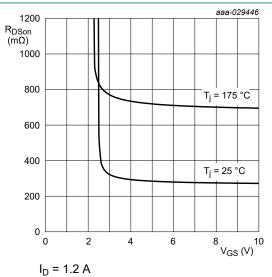


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

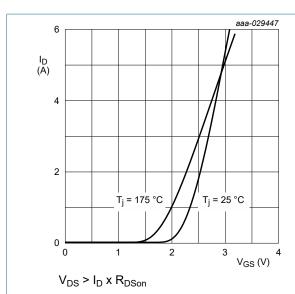


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

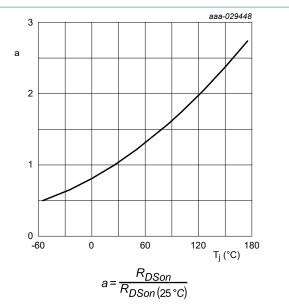


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

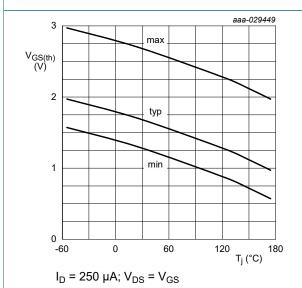


Fig. 12. Gate-source threshold voltage as a function of junction temperature

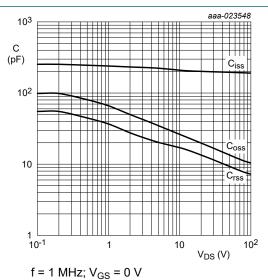


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

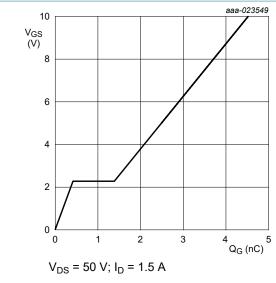


Fig. 14. Gate-source voltage as a function of gate charge; typical values

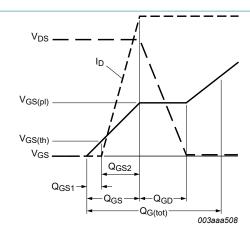


Fig. 15. Gate charge waveform definitions

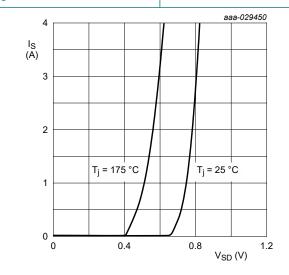
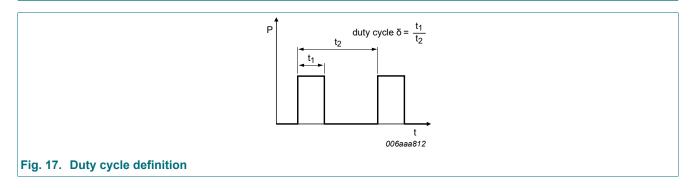


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

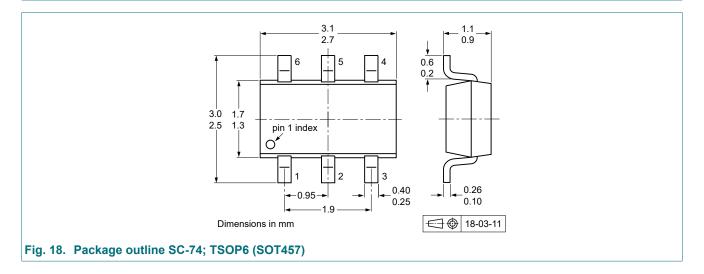
11. Test information



Quality information

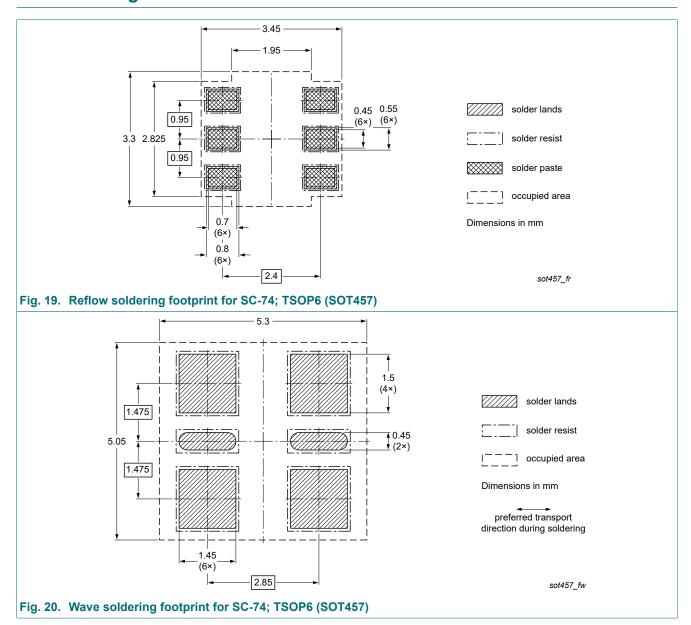
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



100 V, N-channel Trench MOSFET

13. Soldering



100 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN280ENEA v.1	20190411	Product data sheet	-	-

Product data sheet

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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100 V, N-channel Trench MOSFET

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